

Description

The CMD5950 uses advanced trench technology to provide excellent $R_{\text{DS(ON)}}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.

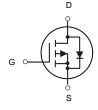


TO-252-2L (DPAK)

General Features

V_{DS} = -100V I_D =-30A

 $R_{DS(ON)} < 57.5~m\Omega$ @ $V_{GS} = -10V$



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
CMD5950	TO-252-2L(DPAK)	5950 XXXX	2500

Absolute Maximum Ratings (T_C=25 ℃ unless otherwise noted)

Symbol	Parameter	ameter Rating	
VDS	Drain-Source Voltage	-100	V
VGS	Gate-Source Voltage	Gate-Source Voltage ±20	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ -30	
IDM	Pulsed Drain Current ²	Pulsed Drain Current ² -120	
P _D @T _C =25°C	Total Power Dissipation ⁴	107	W
Eas	Avalanche energy (Note 2)	Avalanche energy (Note 2) 361	
TSTG	Storage Temperature Range	-55 to 175	°C
TJ	Operating Junction Temperature Range	-55 to 175	°C
R₀JC	Thermal Resistance Junction-Case ¹	1.4	°C/W



Electrical Characteristics (T = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-100	-127		V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V, V _{GS} =0V			-1	μΑ
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.8	-2.5	V
G FS	Forward Transconductance	V _{DS} =-5V, I _D =-15A		50		S
-	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-15A		46	57.5	mΩ
R _{DS(ON)}		V _{GS} =-4.5V, I _D =-10A		48	63	mΩ
Ciss	Input Capacitance			8056		pF
Coss	Output Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1.0MHz		195		pF
Crss	Reverse Transfer Capacitance			70		pF
t _{d(on)}	Turn-on Delay Time			13		nS
t _r	Turn-on Rise Time	V _{GS} =-10V, V _{DS} =-50V,		64		nS
t _{d(off)}	Turn-Off Delay Time	R _L =3.3Ω, R _{GEN} =9.1Ω		36		nS
t _f	Turn-Off Fall Time			52		nS
Qg	Total Gate Charge			147		nC
Qgs	Gate-Source Charge	V _{GS} =-10V, V _{DS} =-50V, I _D =-10A		17		nC
Q_{gd}	Gate-Drain Charge			31		nC
Isp	Source-Drain Current (Body Diode)				-30	Α
VsD	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =-15A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-15A, di/dt=100A/μs		72		ns
Q _{rr}	Reverse Recovery Charge	I _F =-15A, di/dt=100A/μs 120			nC	

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature. Notes 2.E_{AS} condition: T_J =25 $^{\circ}$ C, V_{DD} =50V, V_G =-10V, Rg=25 Ω , L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Characteristics

Figure 1. Output Characteristics

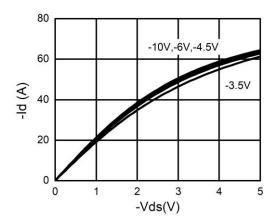


Figure 3. Power Dissipation

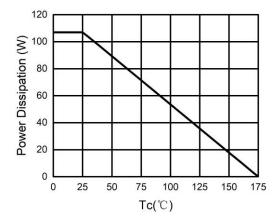


Figure 5. BV_{DSS} vs Junction Temperature

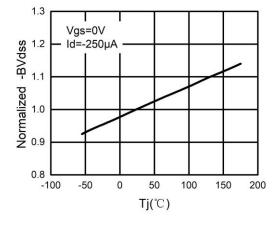


Figure 2. Transfer Characteristics

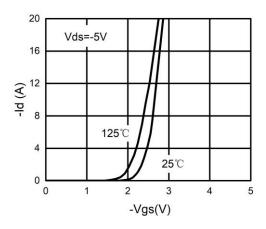


Figure 4. Drain Current

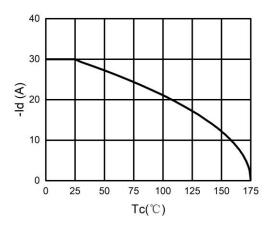


Figure 6. R_{DS(ON)} vs Junction Temperature

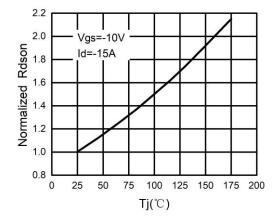


Figure 7. Gate Charge Waveforms

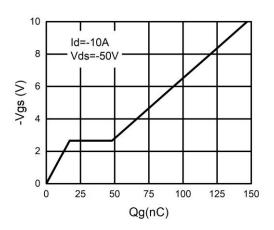


Figure 8. Capacitance

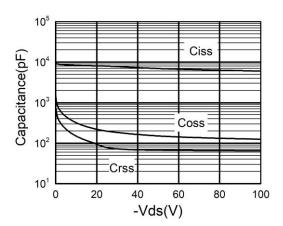


Figure 9. Body-Diode Characteristics

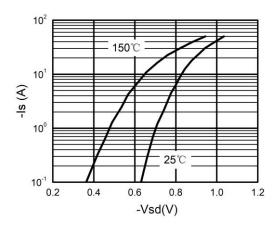
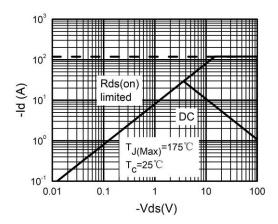


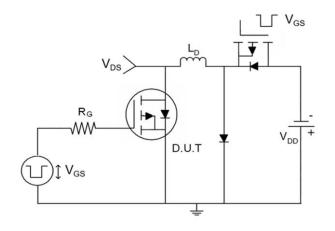
Figure 10. Maximum Safe Operating Area

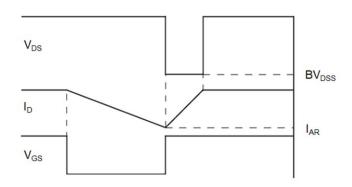




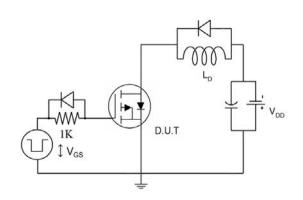
Test Circuit

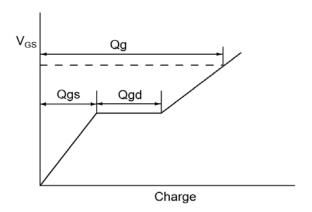
1) E_{AS} Test Circuits



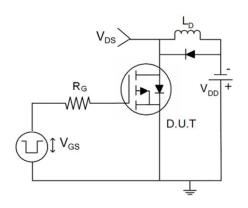


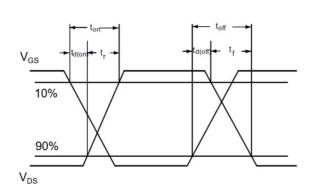
2) Gate Charge Test Circuit





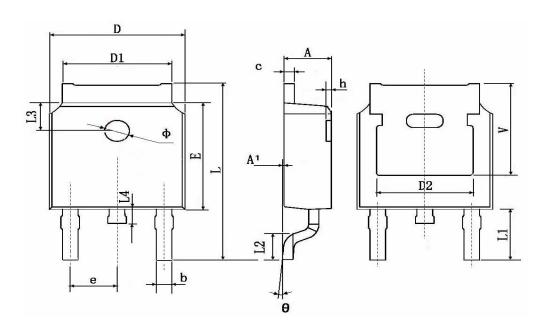
3) Switch Time Test Circuit







TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3		1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	5.350 TYP. 0.211 TYP.		TYP.		



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